Perovskite Solar Cells



1039 Nanotechnology





Tecnologies fotovoltaiques





https://www.nrel.gov/pv/cell-efficiency.html



(various types)

Tecnologies fotovoltaiques

IES-UFIVI (1020X) FING-ISE (117X)



Thin-Film Technologies CIGS (concentrator) CIGS O CdTe ISW Amorphous Si:H (stabilized) **Emerging PV** REL Sanvo O Dye-sensitized cells $|4\chi\rangle$ Perovskite cells (not stabilized) A Perovskite/Si tandem (monolithic) NREL Organic cells (various types) Organic tandem cells Inorganic cells (CZTSSe) Quantum dot cells





Tecnologies fotovoltaiques



Transforming ENERG Sharp (IMM, 302x) Soitec (4-J, 297x) Boeina SolarJunc (LM, 364x) FhG-ISE/ Soitec 46.0% 🗆 (LM. 942x olab FhG-ISE SpireSemicon IREL 44.4% 💙 299x) (MM, 454x) (MM. 406) Boeing-Spectrolab (MM. 240x 327x 319x Boeina-NREL (6-J) SolarJunc Spectrolab (5-39.2% (LM, 418x) Boeing Sharp (IMM) 37.9% Spectrolab NREL (38.1x) 35.5% 🛕 FhG-Ig-Jab LG 32.8% NREL FhG-ISE (117x) NREL (258x) 30.5% A Alta SunPower Alta Radboud Uni Alta Devices Oxford PV 29.1% 28.09 Panasoni Amonix (92x) 27.8% 27.6% ISFH 26.6% 26.19 SolarFron SCAS 23.79 First Solar 23.3% FhG-ISE 21.2% NREL 2015 2005 2010 2020

Multijunction Cells (2-terminal, monolithic)

- LM = lattice matched
- MM = metamorphic
- IMM = inverted, metamorphic
- Three-junction (concentrator)
- Three-junction (non-concentrator)
- ▲ Two-junction (concentrator)
- Two-junction (non-concentrator)
- Four-junction or more (concentrator)
- Four-junction or more (non-concentrator)

Single-Junction GaAs

- ▲ Single crystal
- ▲ Concentrator
- Thin-film crystal

Crystalline Si Cells

- Single crystal (concentrator)
- Single crystal (non-concentrator)
- Multicrystalline
- Thick Si film
- Silicon heterostructures (HIT)
- ▼ Thin-film crystal

https://www.nrel.gov/pv/cell-efficiency.html

http://www.nrel.gov/ncpv/images/efficiency_chart.jpg



Tecnologies fotovoltaiques





M. Green (2016) http://onlinelibrary.wiley.com/doi/10.1002/pip.2788/full



Hybrid halide perovskites: Impact

- -



Source: ISI Web of



General perovskite structure: A BX₃

A = organic component in cuboctahedral A site (MeNH₃⁺, EtNH₃⁺)

B = inorganic components in octahedral B site (Pb_2^+, Sn_2^+)

X = halogens (Cl⁻, Br⁻, I⁻)



D. B. Mitzi, Progress in Inorganic Chemistry 1999

Perovskite structure





- Pb²⁺ is connected to 6 anions I⁻ [PbI₆], which forms an octahedra.
- Each cation CH_3NH_3 + is located at the center of 4 of these octahedra.
- Conduction band, is derived from the Pb 6p orbitals; valence band from I-



Structure



- The crystallographic structure of CH₃NH₃PbI₃ depends on temperature: At low temperature: orthorombic At T> 161.4 K: tetragonal At T >330.4 L: cubic
- > The rotation of CH_3NH_3 + is very fast (ps) in the cubic phase unlike in the orthorombic phase



Hybrid halide perovskites: Versatility

Energy (vs. vacuum, eV)



Rhee et al. NPG Asia Materials (2013) 5, e68





Perovskite solar cells: Cell Preparation Park Method



Perovskite solar cells: Cell Preparation Mitzi-Grätzel Method







Kojima et al., JACS, 2009, 131, 6050-6051

Kim et al., Scientific Reports, 2012, 2, 591

Burschka et al., Nature, 2013, 499, 316–319





Lee et al., Science, 2012, 338, 643-647

No Hole Transporting Media



- Etgar, L.; et al., J. Am. Chem. Soc. 2012, 134, 17396-17399

✓ Devices with MS alumina as an insulating scaffold reports efficiencies higher than 15%.

✓ Samples with no hole transporting material reports efficiencies higher than 12%

✓ It gives evidence of electron and hole transport in PS layer pointing to a different working mechanism than in sensitized devices.

Perovskite solar cells: From sensitized to thin film devices

Thin film solar cell configuration



Liu et al., Nature, 2013, 501(7467),395-8 Eperon et al., Adv. Funct. Mater., 24, 151–157



 ✓ Devices with MS alumina as an insulating scaffold reports efficiencies higher than 15% and thin film configuration over 15%
✓ It gives evidence of carrier transport and accumulation in PS layer

Perovskite solar cells



Mesoporous cell





1 µm

Simone Guarnera et al. J. Phys. Chem. Lett., 2015, 6, 432



Hybrid halide perovskites: morphologies







Perovskite solar cells: Historic Evolution





3.8%

2009

9.7%



2013 15.4%

Perovskite solar cells: Historic Evolution



(10.270)

Seok, Nat. Materials. 2014

Han, Science. 2014, 345, 295-298

Perovskite solar cells: Historic Evolution



May 2014 (17.8%)

Dec 2014 (20.1%)

Sang Il Seok Nature, 2015, 517, 476–480



Perovskita solar cell:



- Eficiències 2013: 15.1% Flat band (Henri Snaith, Oxford University) 15.2% DSC structure (Michael Grätzel, EPFL)
- Eficiències 2015: 18 % Flat band (Henri Snaith, Oxford University) 20.7% DSC structure (Park, KRICT, Michael Grätzel, EPFL)
- Eficiència 2017: 21-22% DSC structure (Michael Grätzel, EPFL, Sang Il Seok, Korea)
- Eficiència 2019: 23.7% DSC structure (Sang Il Seok, Korea)

Perovskite solar cells: Challenges



Snaith, H. J. Phys. Chem. Lett. 2013, 4, 3623-3630

- Stability

- Use of less toxic materials







Photogeneration
Grain boundary rec.
Transport
Interface recombination
Bulk recombination
Charge transfer

Optical properties

ABSORPTION BAND-EDGE



- 1) Sharp band-edge (1.57 eV) > most other comparable semiconductors.
- 2) For $E < E_g$ Urbach tail is observed (slope ≈ 15 meV: very low degree of structural disorder ... high crystallinity in the film). Materials with the smallest Urbach energy lead to the lowest $E_G/q V_{OC}$ values.
- 3) Purely Urbach-exponential trend over more than four decades, suggests no optically detectable deep states.

Stefaan De Wolf *et al.*, *Organometallic Halide Perovskites: Sharp Optical Absorption Edge and Its Relation to Photovoltaic Performance*, J. Phys. Chem. Lett. 2014, 5, 1035–1039

Optical properties

PL-QE and lasing



*Low PLQE at low power due to the presence of defects (long PL decay times).

*Radiative recombination becomes dominant over non radiative at high fluences after defects are filled (short PL decay times).

Felix Deschler, High Photoluminescence Efficiency and Optically Pumped Lasing in Solution-Processed Mixed Halide Perovskite Semiconductors, J. Phys. Chem. Lett. 2014, 5, 1421–1426